Product data sheet

1. General description

NPN low V_{CEsat} Breakthrough in Smal Signal (BISS) transitor in a medium power SOT89 (SC-62) flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5360X

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- · High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- DC-to-DC conversion
- Supply line switching
- · Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- · Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	60	V
I _C	collector current			-	-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	6	Α
R _{CEsat}	collector-emitter saturation resistance	I _C = 2 A; I _B = 200 mA; T _{amb} = 25 °C	[1]	-	-	140	mΩ

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		В
3	В	base	3 2 1	E
			SOT89	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4360X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code			
PBSS4360X	S40			

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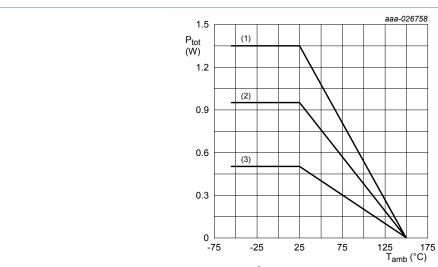
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	80	V
V_{CEO}	collector-emitter voltage	open base		-	60	V
V_{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	3	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	6	Α
I _B	base current			-	500	mA
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	500	mW
			<u>[2]</u>	-	950	mW
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated; mounting pad for collector 1 cm². Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated; mounting pad for collector 6 cm².



- (1) FR4 PCB, single-sided copper, 6 cm²
- (2) FR4 PCB, single-sided copper, 1 cm²
- (3) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
from ju	thermal resistance	in free air	[1]	-	-	250	K/W
	from junction to ambient		[2]	-	-	132	K/W
			[3]	-	-	93	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm².

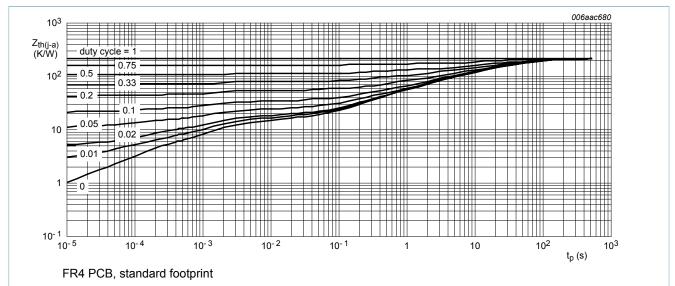
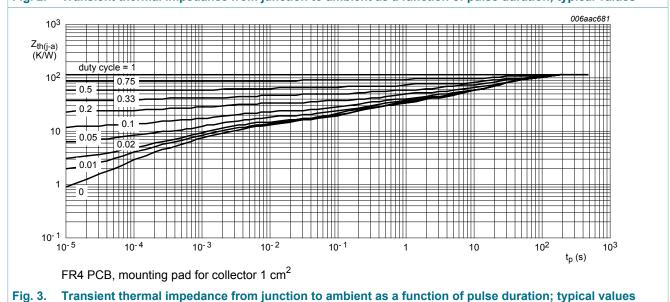
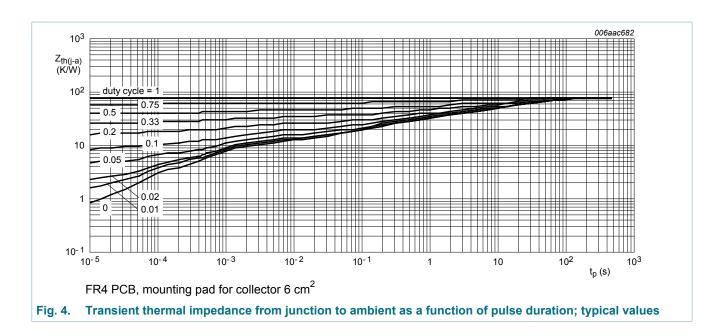


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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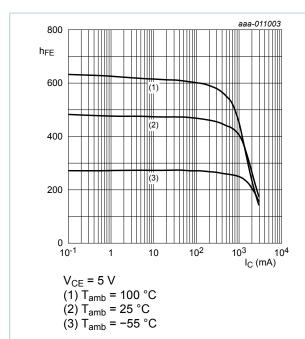
10. Characteristics

Table 7. Characteristics

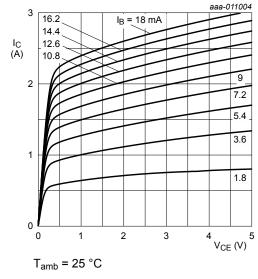
Parameter	Conditions		Min	Тур	Max	Unit
collector-base cut-off	V _{CB} = 48 V; I _E = 0 A; T _{amb} = 25 °C		-	-	100	nA
current	V _{CB} = 48 V; I _E = 0 A; T _j = 150 °C		-	-	50	μΑ
collector-emitter cut-off current	$V_{CE} = 48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	nA
emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
DC current gain	V_{CE} = 5 V; I_{C} = 50 mA; T_{amb} = 25 °C		200	-	-	
	V_{CE} = 5 V; I_{C} = 500 mA; T_{amb} = 25 °C	[1]	200	-	-	
	V _{CE} = 5 V; I _C = 1 A; T _{amb} = 25 °C	[1]	200	-	-	
	V_{CE} = 5 V; I_{C} = 2 A; T_{amb} = 25 °C	[1]	120	-	-	
	V_{CE} = 5 V; I_{C} = 3 A; T_{amb} = 25 °C	[1]	75	-	-	
collector-emitter saturation voltage	I_C = 500 mA; I_B = 50 mA; T_{amb} = 25 °C	[1]	-	-	75	mV
	I_C = 1 A; I_B = 100 mA; T_{amb} = 25 °C	[1]	-	-	150	mV
	I_C = 2 A; I_B = 200 mA; T_{amb} = 25 °C	[1]	-	-	275	mV
	I_C = 3 A; I_B = 300 mA; T_{amb} = 25 °C	[1]	-	-	400	mV
collector-emitter saturation resistance	$I_C = 2 \text{ A}; I_B = 200 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	140	mΩ
base-emitter saturation voltage	$I_C = 1 \text{ A}; I_B = 100 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	1.2	V
base-emitter turn-on voltage	V_{CE} = 5 V; I_{C} = 1 A; T_{amb} = 25 °C	[1]	-	-	1.1	V
transition frequency	V_{CE} = 10 V; I_{C} = 50 mA; f = 100 MHz; T_{amb} = 25 °C		75	145	-	MHz
collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	11	14	pF
	collector-base cut-off current collector-emitter cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage base-emitter saturation voltage base-emitter turn-on voltage transition frequency	$ \begin{array}{c} \text{collector-base cut-off} \\ \text{current} \end{array} $	$ \begin{array}{c} \text{collector-base cut-off} \\ \text{current} \\ \end{array} \begin{array}{c} V_{CB} = 48 \ \text{V}; \ I_{E} = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \\ V_{CB} = 48 \ \text{V}; \ I_{E} = 0 \ \text{A}; \ T_{j} = 150 \ ^{\circ}\text{C} \\ \end{array} \\ \end{array} \\ \begin{array}{c} \text{collector-emitter cut-off} \\ \text{current} \\ \end{array} \begin{array}{c} V_{CE} = 48 \ \text{V}; \ V_{BE} = 0 \ \text{V}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \end{array} \\ \begin{array}{c} \text{collector-emitter cut-off} \\ \text{current} \\ \end{array} \\ \begin{array}{c} V_{CE} = 48 \ \text{V}; \ V_{BE} = 0 \ \text{V}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \end{array} \\ \begin{array}{c} V_{CE} = 5 \ \text{V}; \ I_{C} = 0 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{c} V_{CE} = 5 \ \text{V}; \ I_{C} = 500 \ \text{mA}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{c} V_{CE} = 5 \ \text{V}; \ I_{C} = 500 \ \text{mA}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{c} V_{CE} = 5 \ \text{V}; \ I_{C} = 2 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{c} I_{1} \\ V_{CE} = 5 \ \text{V}; \ I_{C} = 3 \ \text{A}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{c} I_{1} \\ I_{C} = 500 \ \text{mA}; \ I_{B} = 50 \ \text{mA}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{c} I_{1} \\ I_{C} = 1 \ \text{A}; \ I_{B} = 100 \ \text{mA}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{c} I_{1} \\ I_{C} = 2 \ \text{A}; \ I_{B} = 200 \ \text{mA}; \ T_{amb} = 25 \ ^{\circ}\text{C} \\ \end{array} \\ \begin{array}{c} I_{1} \\ I_{C} = 2 \ \text{A}; \ I_{B} = 200 \ \text{mA}; 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^[1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$

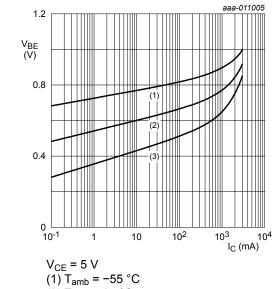
60 V, 3 A NPN low VCEsat BISS transistor



DC current gain as a function of collector Fig. 5. current; typical values

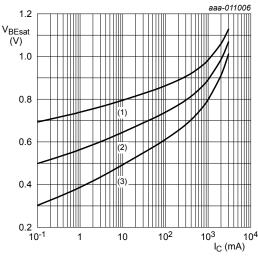


Collector current as a function of collector-Fig. 6. emitter voltage; typical values



(2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = 100 \,^{\circ}C$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



 $I_C/I_B = 20$ (1) $T_{amb} = -55$ °C

(2) T_{amb} = 25 °C (3) T_{amb} = 100 °C

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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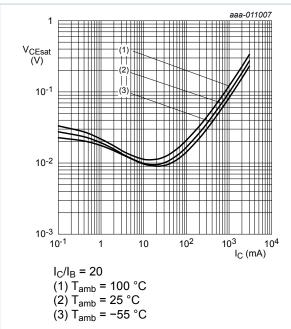


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

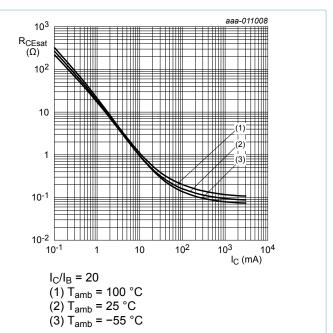


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

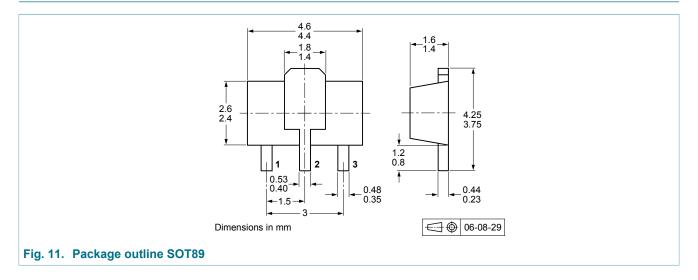
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11. Test information

Quality information

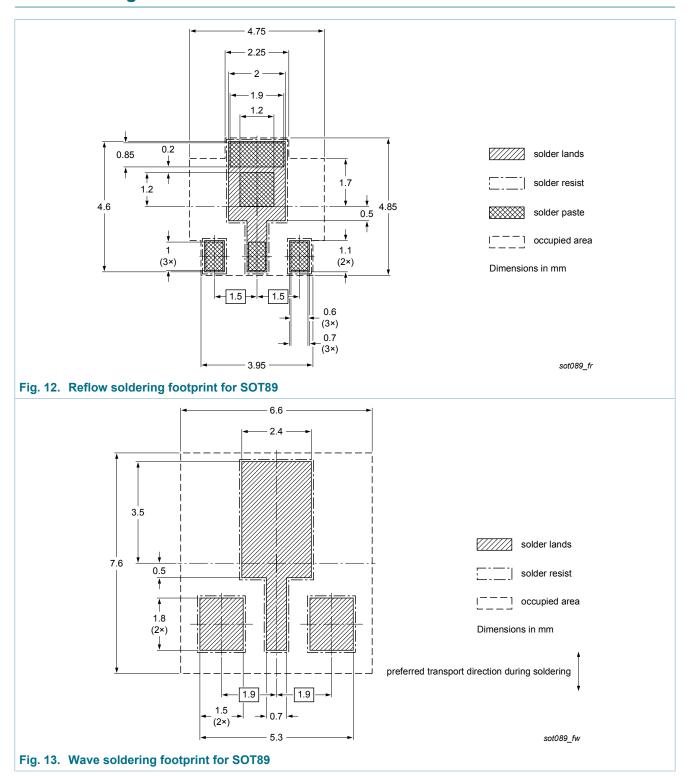
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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60 V, 3 A NPN low VCEsat BISS transistor

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4360X v.1	20170609	Product data sheet	-	-

60 V, 3 A NPN low VCEsat BISS transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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